# **BUK7K52-60E**

# Dual N-channel 60 V, 45 m $\Omega$ standard level MOSFET

**10 December 2013** 

**Product data sheet** 

# 1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V<sub>GS(th)</sub> of greater than 1 V at 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	15.4	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	32	W
Static characte	Static characteristics FET1 and FET2						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	35	45	mΩ
Dynamic characteristics FET1 and FET2							
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 13}}; \underline{\text{Fig. 14}}$		-	3.5	-	nC



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2	

# 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK7K52-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7K52-60E	75260E

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	60	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC	-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	15.4	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	-	12.6	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4	-	71	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	32	W

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Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						
Is	source current	T <sub>mb</sub> = 25 °C		-	15.4	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s; T_{mb} = 25 \ ^{\circ}C$		-	71	Α
Avalanche Ruggedness FET1 and FET2						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 15.4 A; $V_{sup} \le 60 \text{ V}$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3	[1][2]	-	11.6	mJ

- 1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

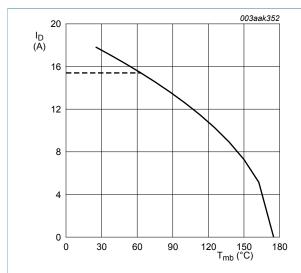


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$ 

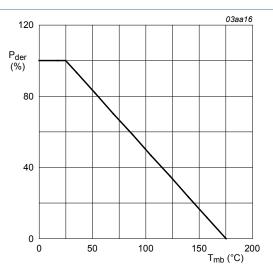


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times 100 \%$$

#### Dual N-channel 60 V, 45 m $\Omega$ standard level MOSFET

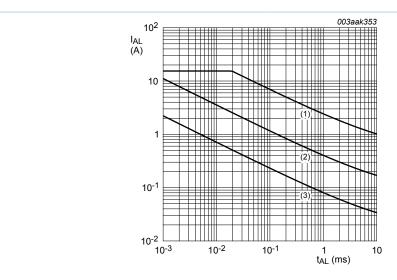
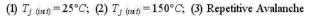


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



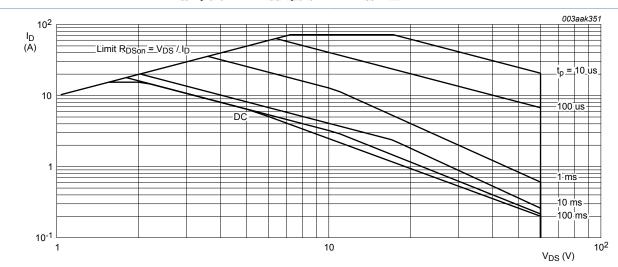


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

## 9. Thermal characteristics

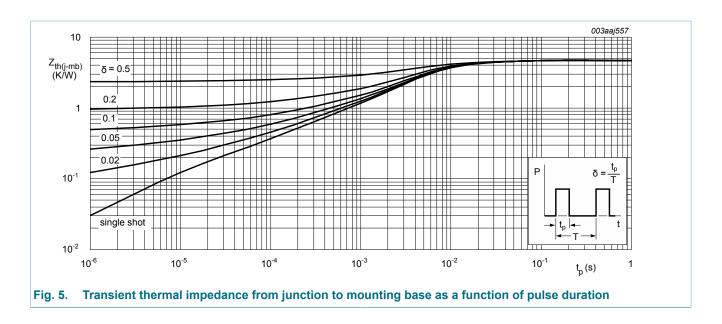
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 5	-	-	4.68	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics FET1 and FET2					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 ^{\circ}C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9; Fig. 10	1	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9; Fig. 10	-	-	4.5	V	
I <sub>DSS</sub> drain le	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μΑ
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 11$	-	35	45	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	78	101	mΩ
Dynamic ch	aracteristics FET1 and FE	T2	,			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	9.2	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13; Fig. 14</u>	-	2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	3.5	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{GS(pl)}$	gate-source plateau voltage	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 48 V; T <sub>j</sub> = 25 °C; Fig. 13; Fig. 14	-	5	-	V
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	401	535	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	73	87	pF
C <sub>rss</sub>	reverse transfer capacitance		-	53	72	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 48 V; $R_{L}$ = 5 $\Omega$ ; $V_{GS}$ = 10 V; $R_{G(ext)}$ = 5 $\Omega$ ; $T_{j}$ = 25 °C; $I_{D}$ = 5 A	-	4.3	-	ns
t <sub>r</sub>	rise time		-	5.1	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	8.4	-	ns
t <sub>f</sub>	fall time		-	5.4	-	ns
Source-dra	ain diode FET1 and FET2			l l		
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	17.6	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	12.3	-	nC

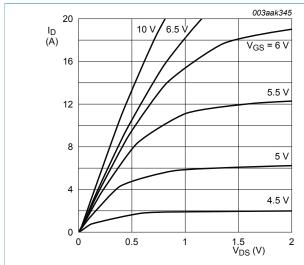


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

 $T_j = 25^{\circ}C$ 

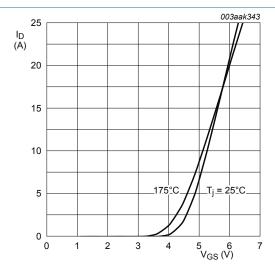


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

 $V_{DS} = 10V$ 

### Dual N-channel 60 V, 45 m $\Omega$ standard level MOSFET

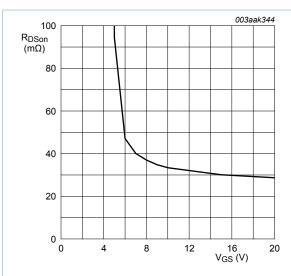


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C;  $I_D = 5A$ 

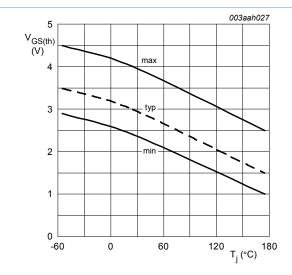


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

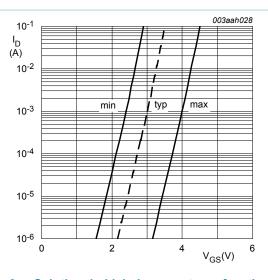


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

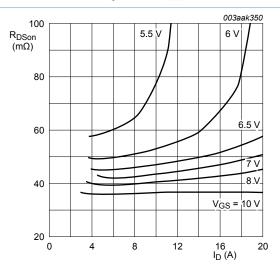


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

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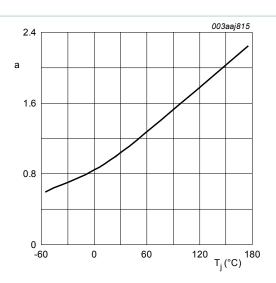


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

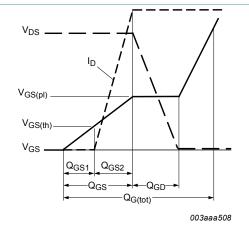


Fig. 14. Gate charge waveform definitions

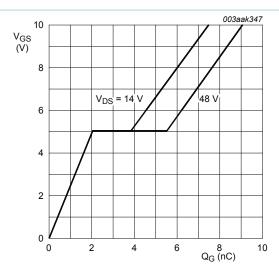


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; \ I_D = 5A$$

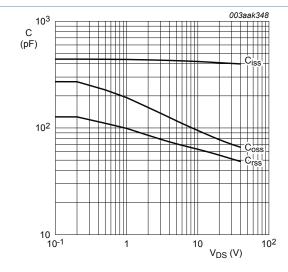


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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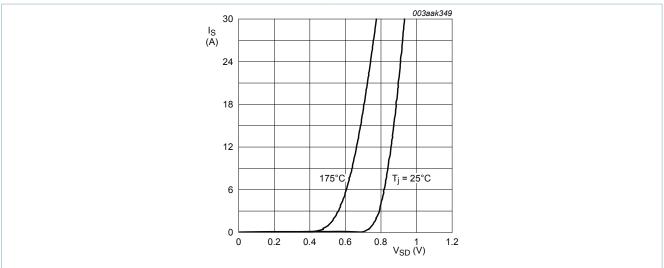


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

#### Dual N-channel 60 V, 45 mΩ standard level MOSFET

# 11. Package outline

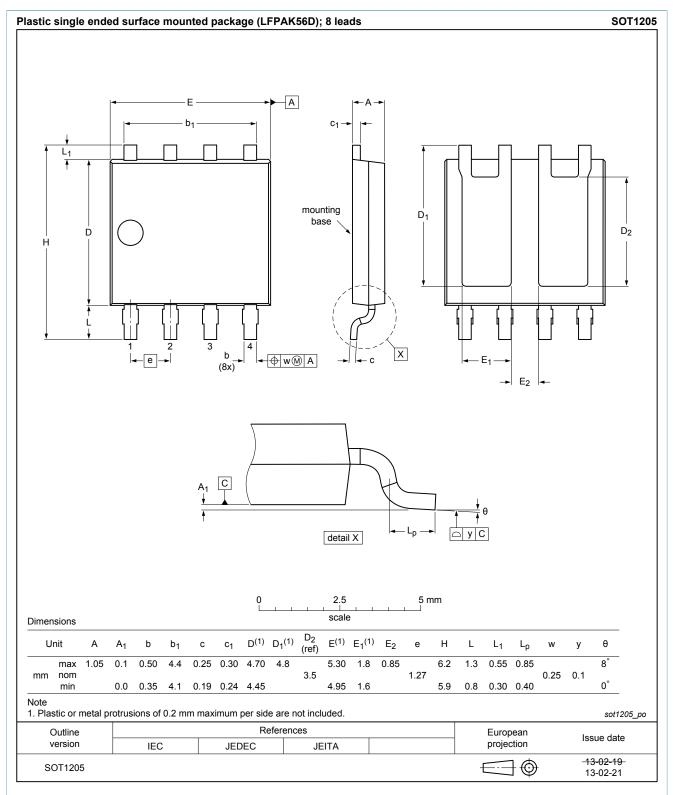


Fig. 17. Package outline LFPAK56D (SOT1205)

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